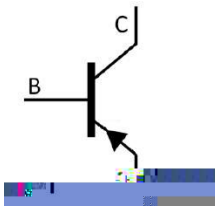
WR0<5+U, ṂṂÞ SQS ÆṀ ч s ‖ ㄱ Silicon PNP transistor in a TO-92(R) Plastic Package.

ㅊ Ɔ я /ль EF879 Йį ´
High voltage, complementary to BC546.

ᵮ ˇ ѽ ᶻ ȝ Ầ ԋ
General purpose and switching application.

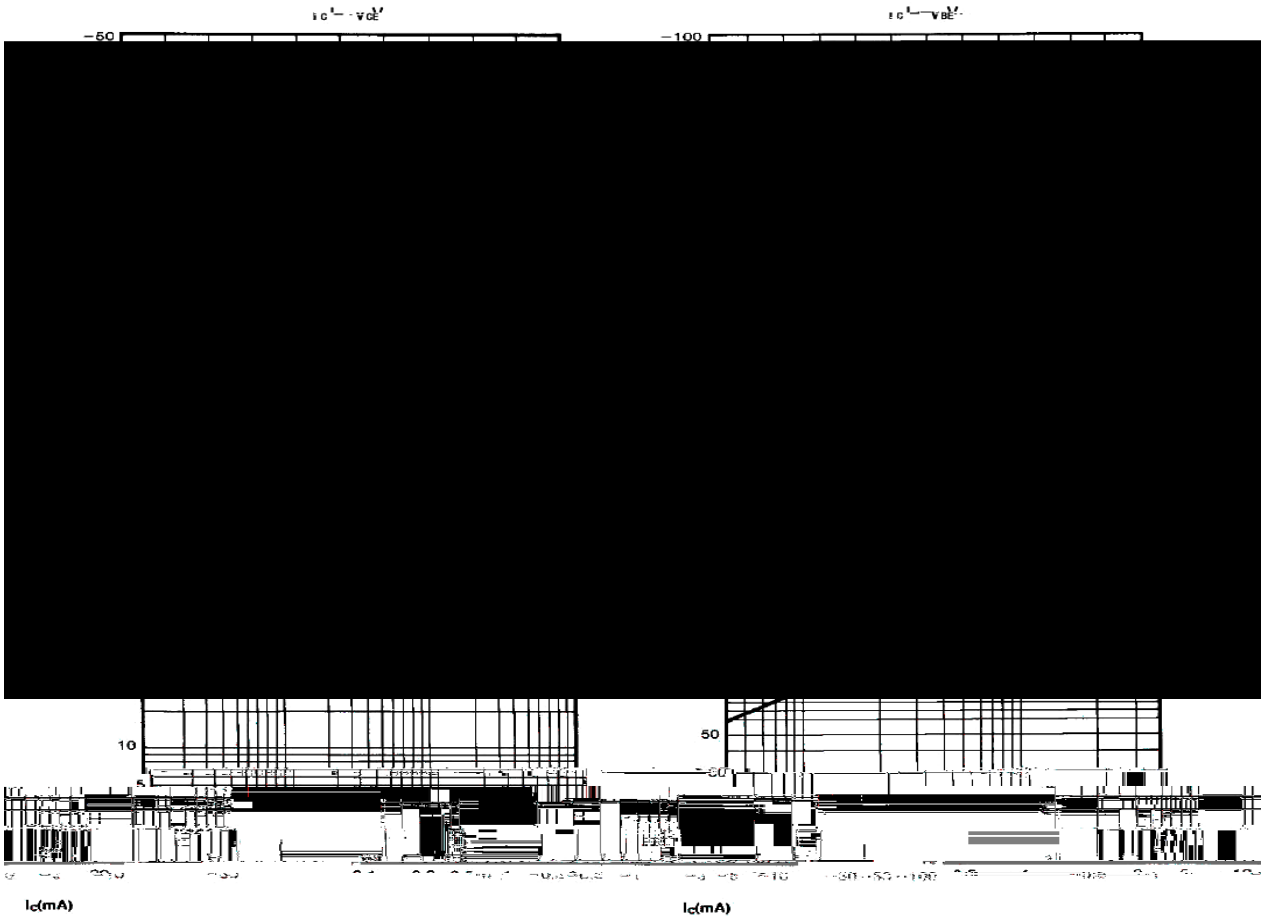


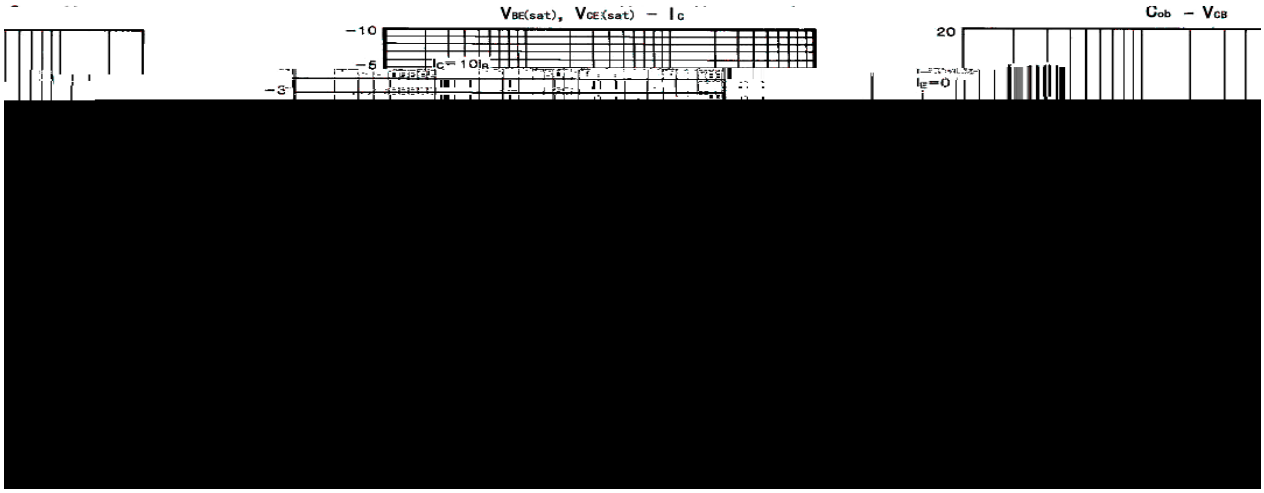


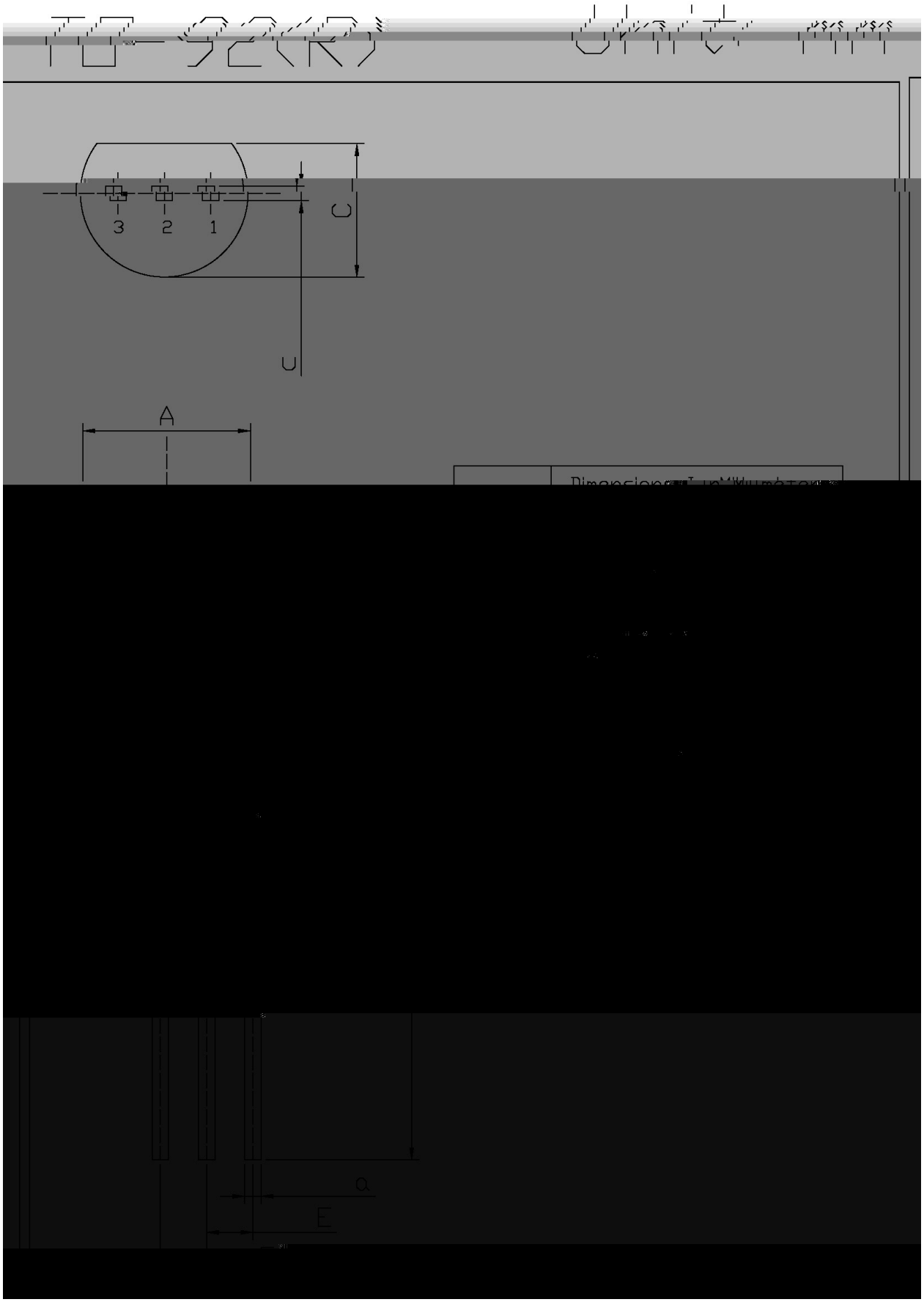
PIN1 χ Emitter PIN 2 χ

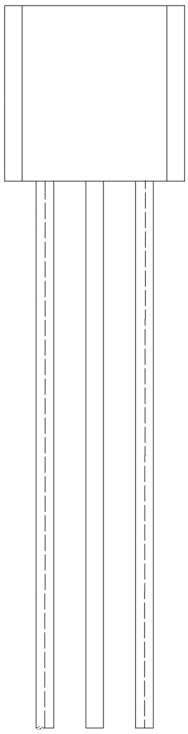
v ̈Ω Parameter	ϒ N Symbol	̈Ω Ö Rating	D Ч Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-65	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current - Continuous	I_C	-100	mA
Emitter Current - Continuous	I_E	100	mA
Collector Power Dissipation	P_C	625	mW
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-55 150	

v ̈Ω Parameter	ϒ N Symbol	Ш ;ϯ Ţ Test Conditions	ѡ ṇ Ö Min	Ɛ ʒ Ö Typ	ѡ ᶻ Ö Max	D Ч Unit
Collector Cut-Off Current	I_{CBO}	V_{CB}=-30V I_E=0			-0.015	μA


−50
−100
10
50
Ic(mA)
Ic(mA)


VBE(sat), VCE(sat) − Ic
−10
−5
−3
Ic= 10IB
Cob − VCB
20
IE=0


3
2
1
C
U
A
Q
E





ب ˝ χ

1 Ĺ ♬ □ ỷ 25 Ḱ 150 ɬ ı `H ڑ 60 Ḱ 90sec;

2 Š Ө □ ỷ 255 ° 5 ɬ ı `H ڑ `Y ﾉ ᎏ 5 ° 0.5sec;

3 ì ˙ ϒ ˛ ɔ ଌ ỷ ᎏ 2 Ḱ 10 ɬ /sec.

Note:

1.Preheating:25~150 ɬ , Time:60~90sec.

2.Peak Temp.:255 ° 5 ɬ , Duration:5 ° 0.5sec.

3. Cooling Speed: 2~10 ɬ /sec.

□ ỷ χ 270 ° 5 ɬ `H ڑ χ 10 ° 1 sec. Temp.:270±5 Time:10±1 sec

¨Ω ţ ɣ Ь / BULK

Package Type	Units					Dimension		(unit mm3)
	Units/Bag /	Bags/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

ﾉ V ɣ Ь / AMMO

Package Type	Units					Dimension	(unit mm3)
	Units/tape /	Tape/Inner Box /	Rows/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Inner Box	Outer Box
TO-92	3,000	1	120	10	30,000	328×230×42	480×346×235 547×407×268